



**2SJ636**

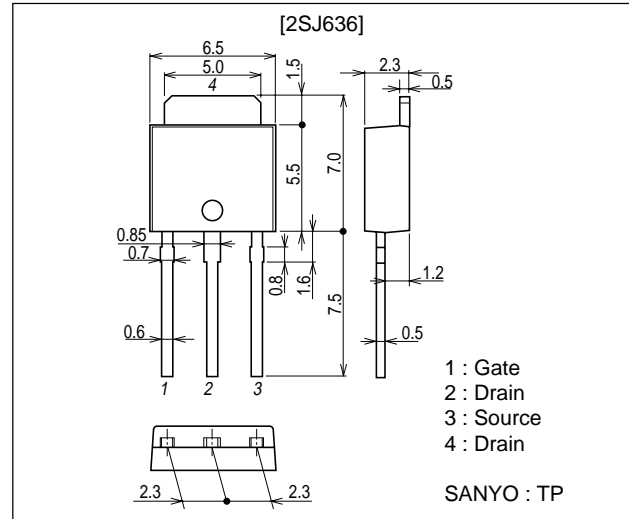
## DC / DC Converter Applications

### Features

- Low ON-resistance.
- Ultrahigh-speed switching.
- 4V drive.

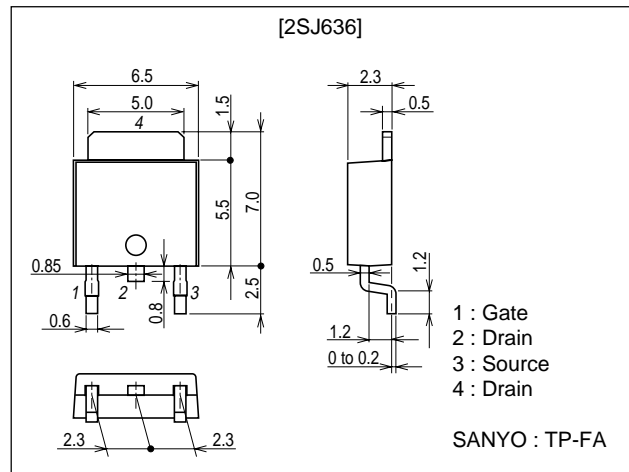
### Package Dimensions

unit : mm  
2083B



### Package Dimensions

unit : mm  
2092B



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## Specifications

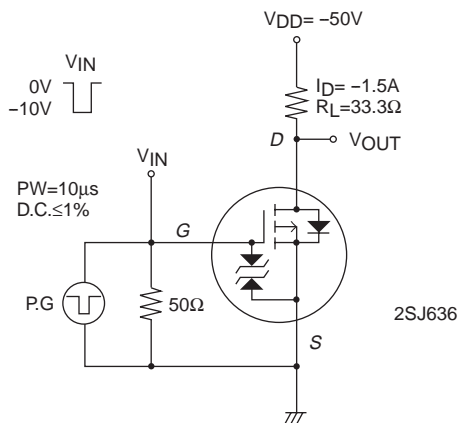
### Absolute Maximum Ratings at Ta=25°C

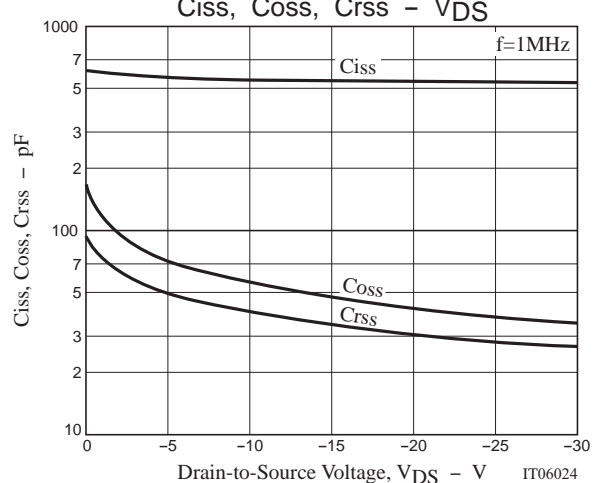
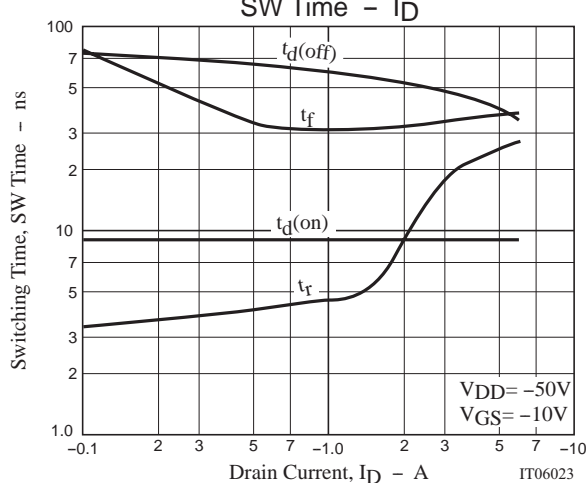
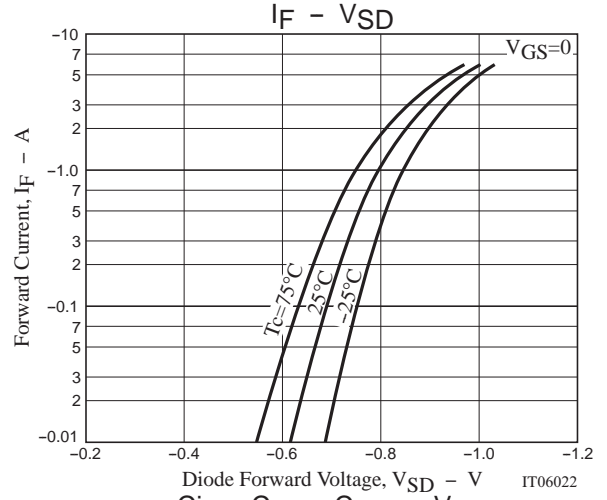
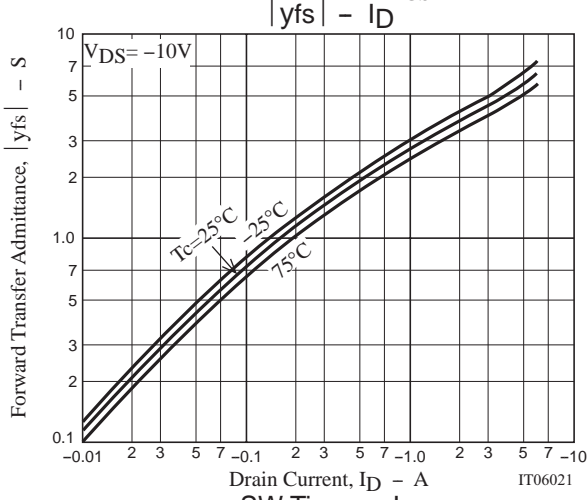
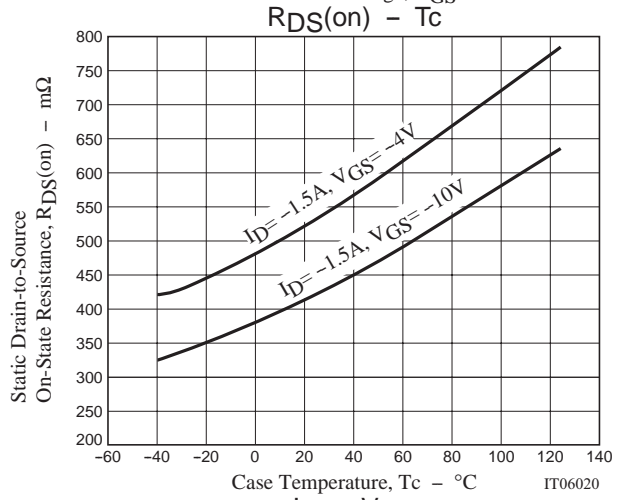
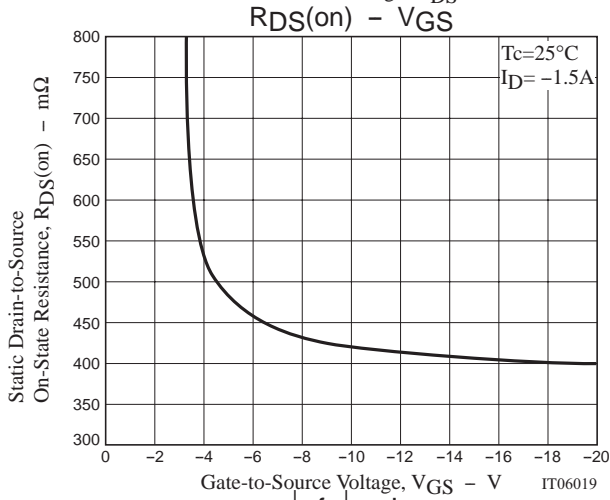
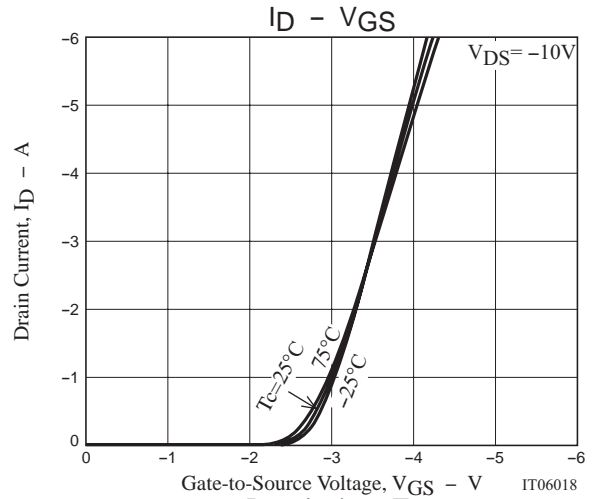
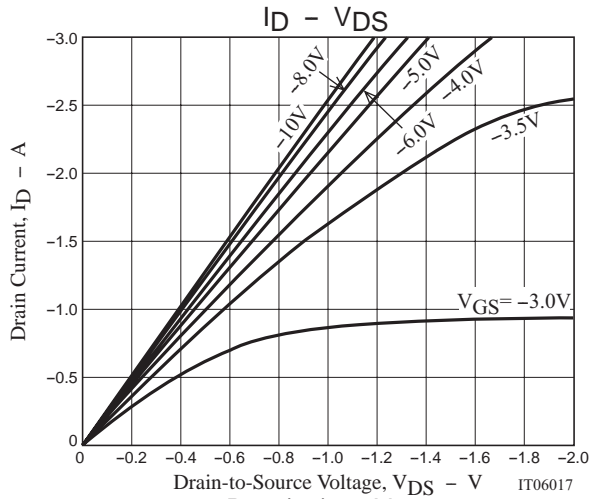
Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V <sub>DSS</sub>		-100	V
Gate-to-Source Voltage	V <sub>GSS</sub>		±20	V
Drain Current (DC)	I <sub>D</sub>		-3	A
Drain Current (Pulse)	I <sub>DP</sub>	PW≤10μs, duty cycle≤1%	-12	A
Allowable Power Dissipation	P <sub>D</sub>		1	W
		T <sub>c</sub> =25°C	15	W
Channel Temperature	T <sub>ch</sub>		150	°C
Storage Temperature	T <sub>stg</sub>		-55 to +150	°C

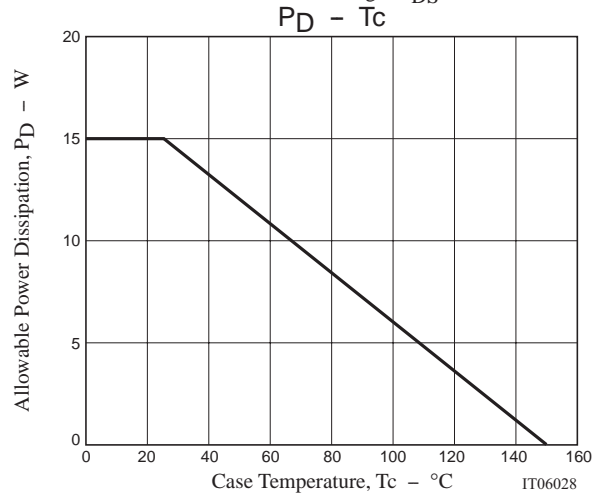
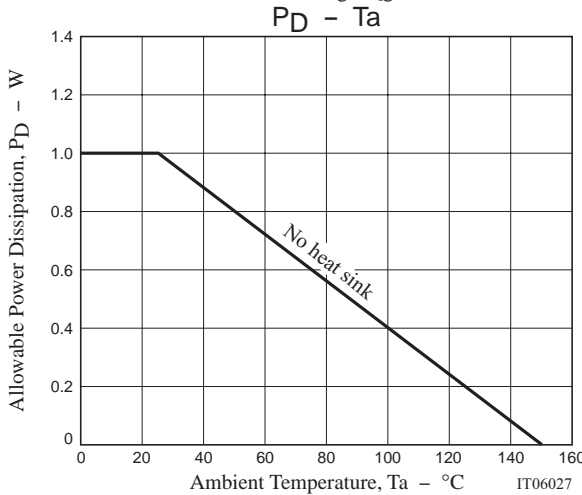
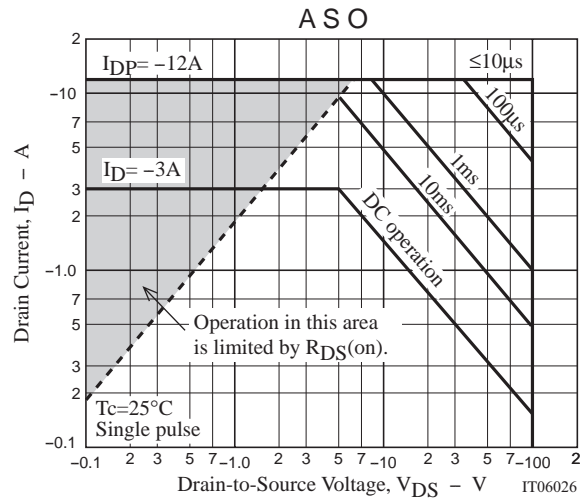
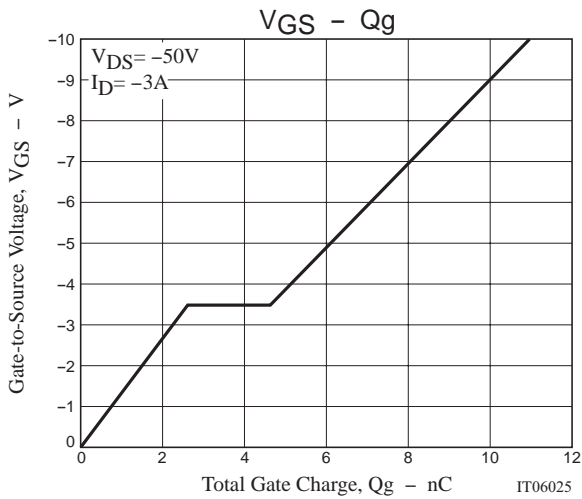
### Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> =-1mA, V <sub>GS</sub> =0	-100			V
Zero-Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-100V, V <sub>GS</sub> =0			-1	μA
Gate-to-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±16V, V <sub>DS</sub> =0			±10	μA
Cutoff Voltage	V <sub>GS(off)</sub>	V <sub>DS</sub> =-10V, I <sub>D</sub> =-1mA	-1.2		-2.6	V
Forward Transfer Admittance	y <sub>fs</sub>	V <sub>DS</sub> =-10V, I <sub>D</sub> =-1.5A	1.5	3		S
Static Drain-to-Source On-State Resistance	R <sub>DS(on)1</sub>	I <sub>D</sub> =-1.5A, V <sub>GS</sub> =-10V		415	535	mΩ
	R <sub>DS(on)2</sub>	I <sub>D</sub> =-1.5A, V <sub>GS</sub> =-4V		535	735	mΩ
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =-20V, f=1MHz		535		pF
Output Capacitance	C <sub>oss</sub>	V <sub>DS</sub> =-20V, f=1MHz		43		pF
Reverse Transfer Capacitance	C <sub>rss</sub>	V <sub>DS</sub> =-20V, f=1MHz		31		pF
Turn-ON Delay Time	t <sub>d(on)</sub>	See specified Test Circuit.		9		ns
Rise Time	t <sub>r</sub>	See specified Test Circuit.		15		ns
Turn-OFF Delay Time	t <sub>d(off)</sub>	See specified Test Circuit.		56		ns
Fall Time	t <sub>f</sub>	See specified Test Circuit.		35		ns
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =-50V, V <sub>GS</sub> =-10V, I <sub>D</sub> =-3A		11		nC
Gate-to-Source Charge	Q <sub>gs</sub>	V <sub>DS</sub> =-50V, V <sub>GS</sub> =-10V, I <sub>D</sub> =-3A		2.6		nC
Gate-to-Drain "Miller" Charge	Q <sub>gd</sub>	V <sub>DS</sub> =-50V, V <sub>GS</sub> =-10V, I <sub>D</sub> =-3A		2		nC
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =-3A, V <sub>GS</sub> =0	-0.9	-1.2		V

### Switching Time Test Circuit







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